

DMP6250SFDFWQ-13R-VB Datasheet

P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ)
- 60	0.085 at $V_{GS} = -10$ V	- 5	34
	0.100 at $V_{GS} = -4.5$ V	- 4	

FEATURES

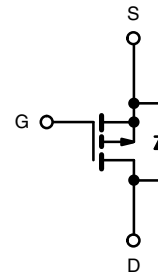
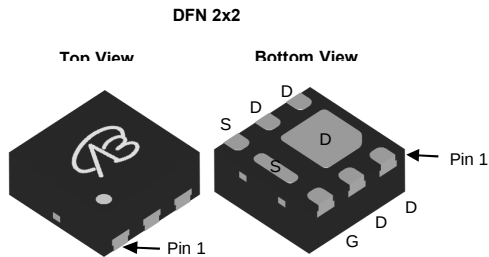
- Halogen-free According to IEC 61249-2-21 Definition
- Trench Power MOSFET
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- High Side Switch for Full Bridge Converter
- DC/DC Converter for LCD Display



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise note)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current	I_{DM}	- 15	
Avalanche Current, Single Pulse	I_{AS}	- 22	
Repetitive Avalanche Energy, Single Pulse ^a	E_{AS}	24.2	mJ
Power Dissipation	P_D	$T_C = 25$ °C	W
		$T_A = 25$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	17	21	°C/W
		45	55	
Maximum Junction-to-Case	R_{thJC}	2.7	3.25	

Notes:

- Duty cycle ≤ 1 %.
- When mounted on 1" square PCB (FR-4 material).
- See SOA curve for voltage derating.
- Based up on $T_C = 25$ °C.

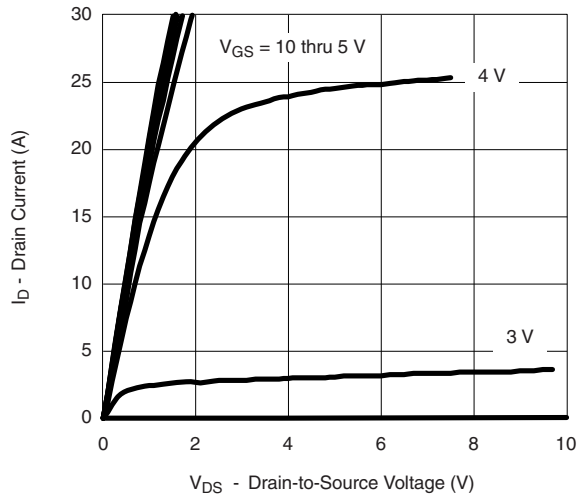
SPECIFICATIONS (T _J = 25 °C, unless otherwise note)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 48 V, V _{GS} = 0 V, T _J = 125 °C			- 50	
		V _{DS} = - 48 V, V _{GS} = 0 V, T _J = 150 °C			- 125	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 20			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 10 A		0.085		Ω
		V _{GS} = - 10 V, I _D = - 10 A, T _J = 125 °C		0.127		
		V _{GS} = - 10 V, I _D = - 10 A, T _J = 150 °C		0.170		
		V _{GS} = - 4.5 V, I _D = - 5 A		0.100		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 10 A		22		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = - 25 V, f = 1 MHz		1000		pF
Output Capacitance	C _{oss}			130		
Reverse Transfer Capacitance	C _{rss}			90		
Total Gate Charge ^c	Q _g	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 10 A		30	40	nC
Gate-Source Charge ^c	Q _{gs}			4.5		
Gate-Drain Charge ^c	Q _{gd}			7		
Gate Resistance	R _g	f = 1 MHz		7		Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 30 V, R _L = 3 Ω I _D ≅ - 19 A, V _{GEN} = - 10 V, R _g = 2.5 Ω		8	15	ns
Rise Time ^c	t _r			9	15	
Turn-Off Delay Time ^c	t _{d(off)}			65	100	
Fall Time ^c	t _f			30	45	
Drain-Source Body Diode and Characteristics (T _C = 25 °C) ^b						
Continuous Current	I _S				- 5	A
Pulsed Current	I _{SM}				- 15	
Forward Voltage ^a	V _{SD}	I _F = - 19 A, V _{GS} = 0 V		-1	-1.5	V
Reverse Recovery Time	t _{rr}	I _F = - 19 A, di/dt = 100 A/μs		41	61	ns

Notes:

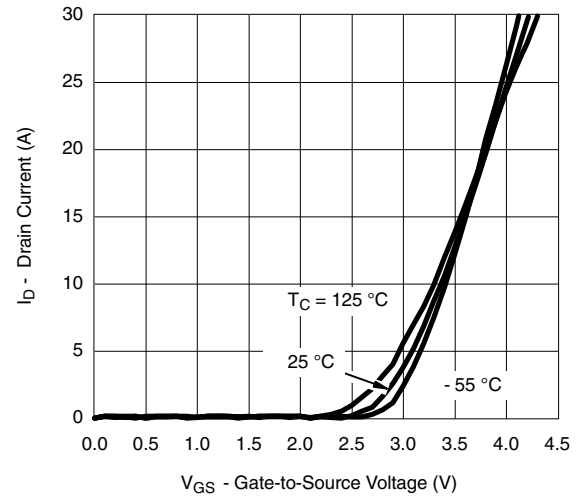
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

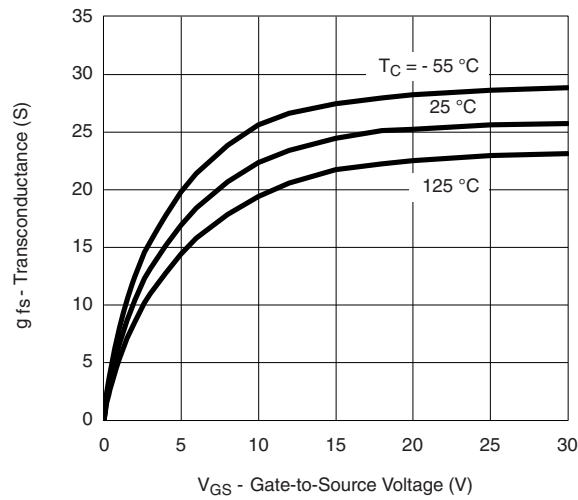
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



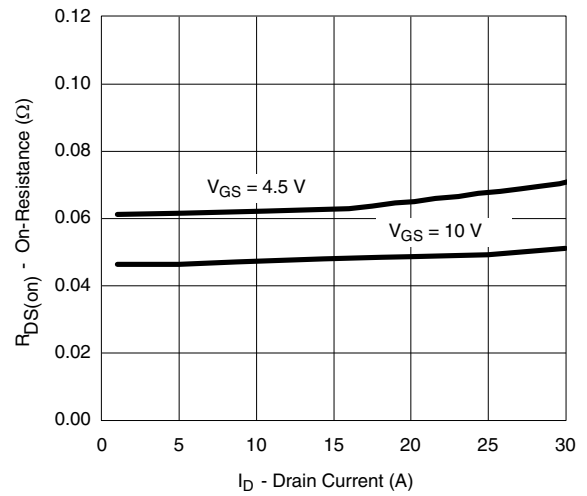
Output Characteristics



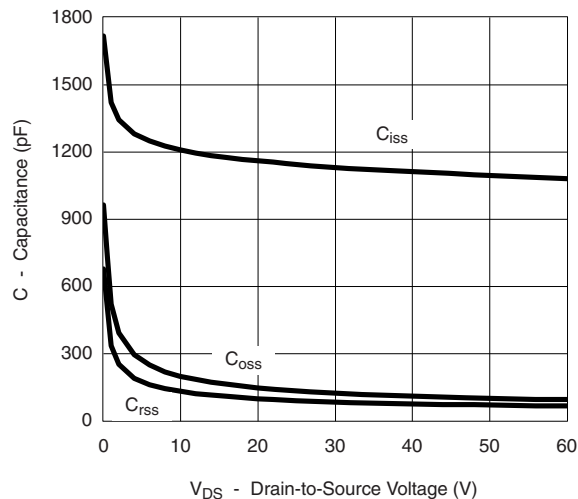
Transfer Characteristics



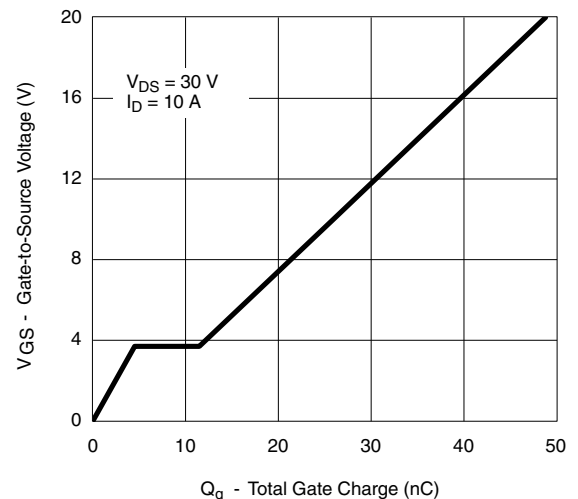
Transconductance



On-Resistance vs. Drain Current

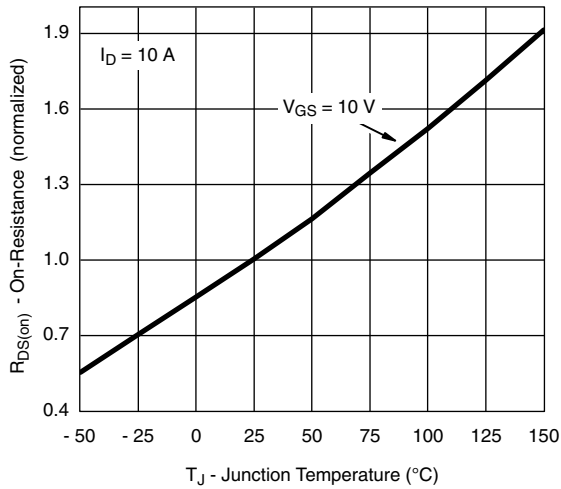


Capacitance

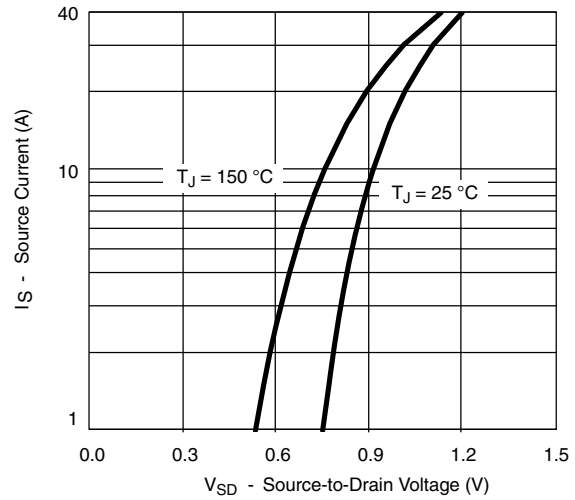


Gate Charge

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

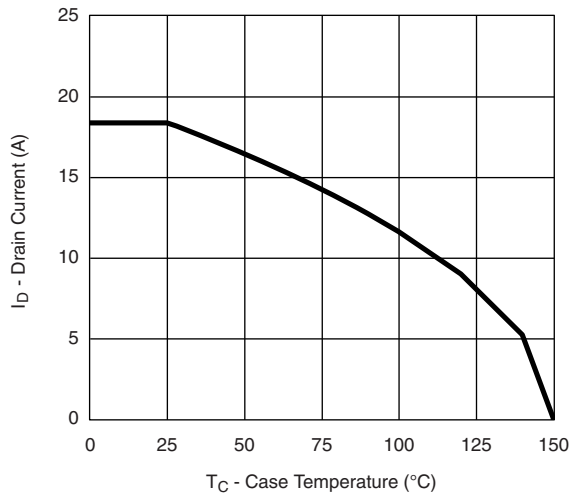


On-Resistance vs. Junction Temperature

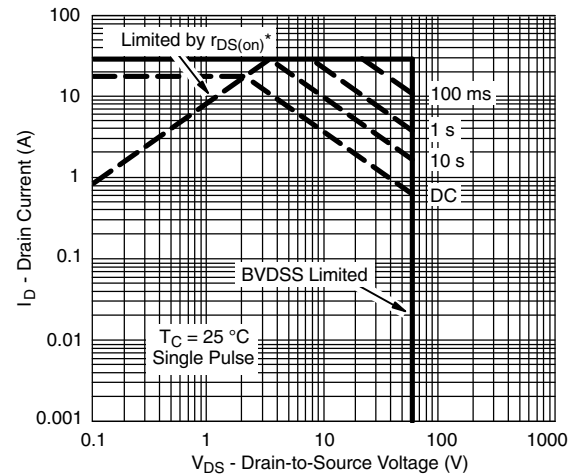


Source-Drain Diode Forward Voltage

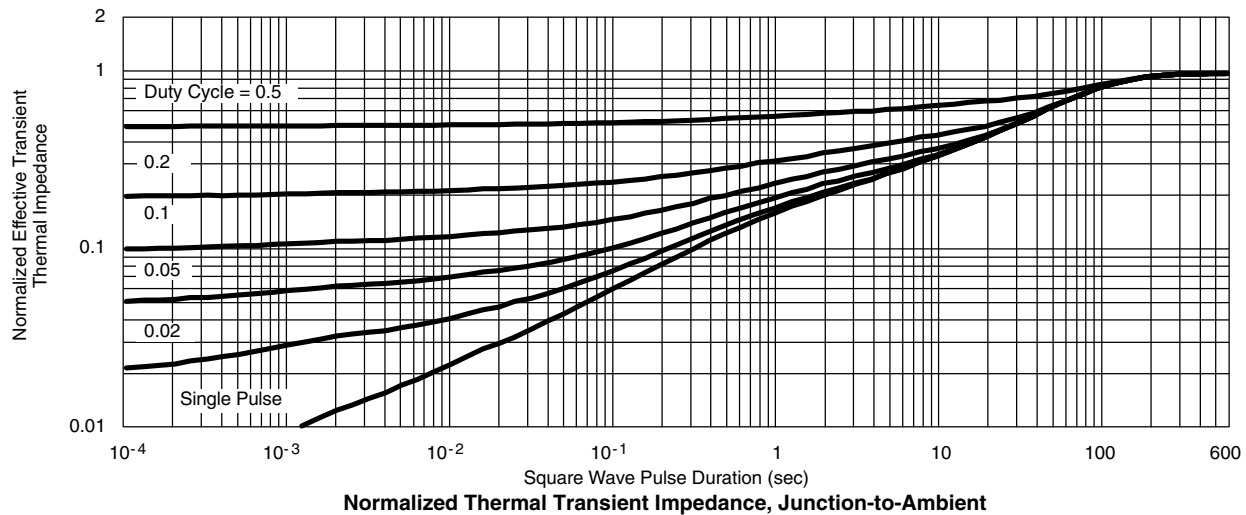
THERMAL RATINGS



Maximum Drain Current
vs. Case Temperature

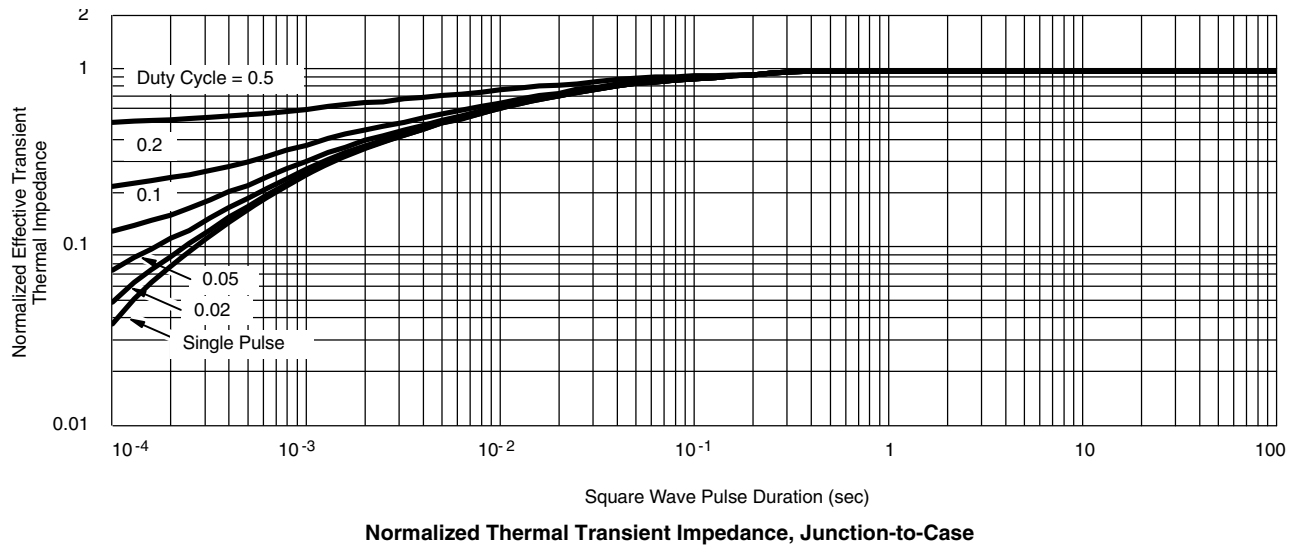


* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified
Safe Operating Area

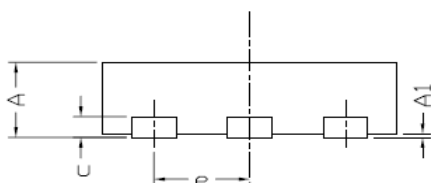
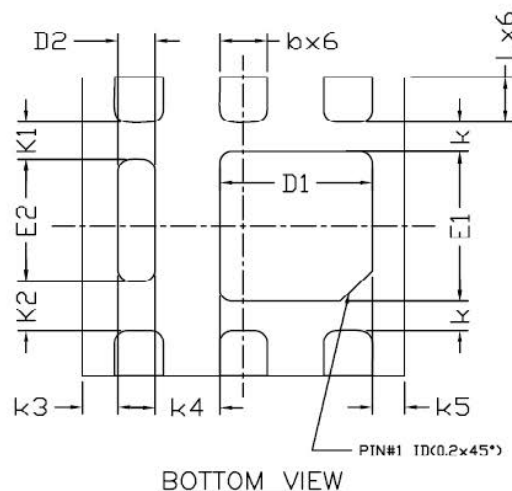
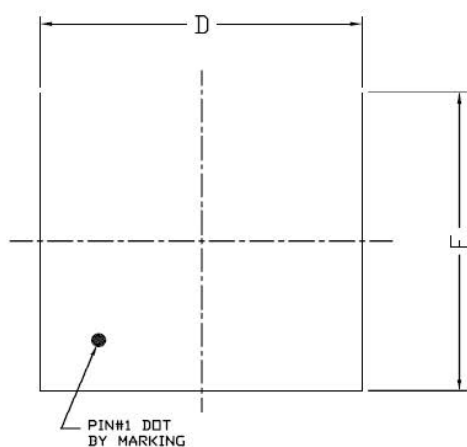


Normalized Thermal Transient Impedance, Junction-to-Ambient

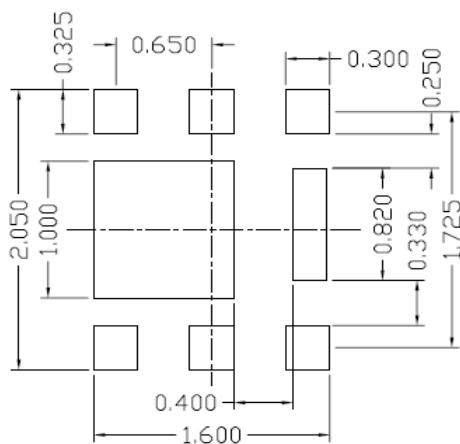
THERMAL RATINGS



DFN2x2 _6L_EP1_S PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



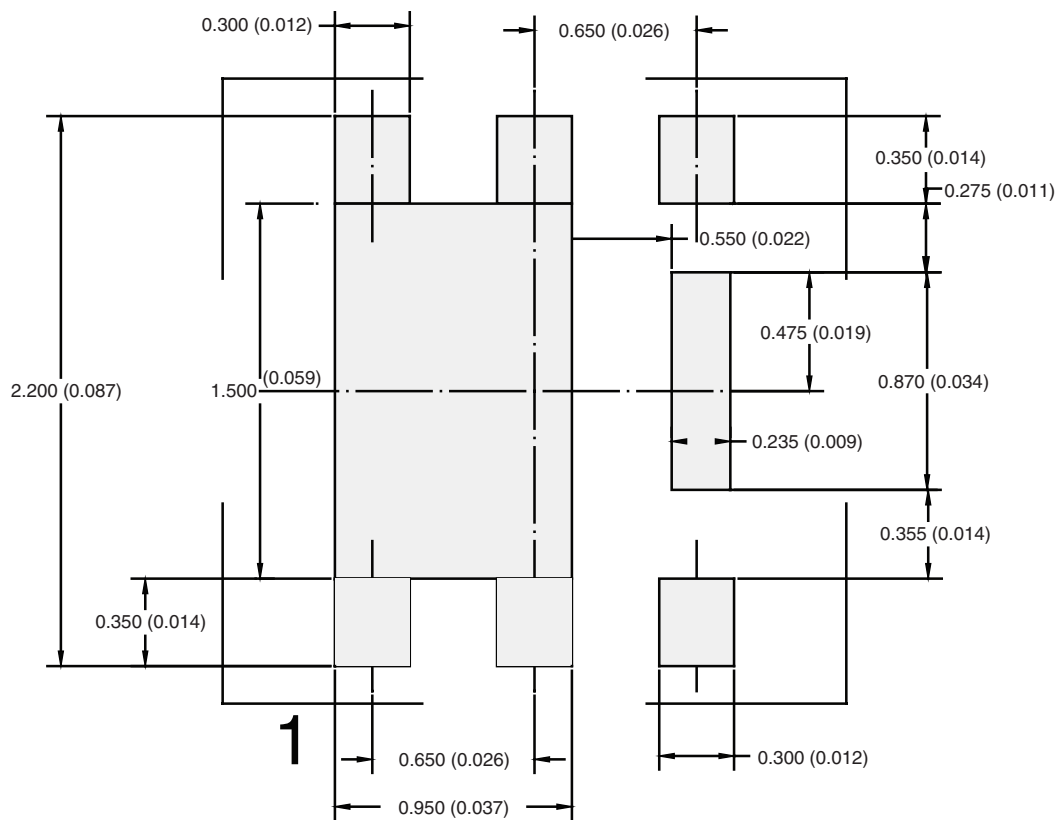
UNIT: mm

NOTE

1. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.022	0.024
A1	0.00	—	0.05	0.000	—	0.002
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.152 REF			0.006 REF		
D	1.90	2.00	2.10	0.075	0.079	0.083
D1	0.85	0.95	1.05	0.033	0.037	0.041
D2	0.13	0.23	0.33	0.005	0.009	0.013
E	1.90	2.00	2.10	0.075	0.079	0.083
E1	0.90	1.00	1.10	0.035	0.039	0.043
E2	0.72	0.82	0.92	0.028	0.032	0.036
e	0.65 BSC			0.026 BSC		
K	0.20 BSC			0.008 BSC		
K1	0.25 BSC			0.010 BSC		
K2	0.33 BSC			0.013 BSC		
K3	0.22 BSC			0.009 BSC		
K4	0.40 BSC			0.016 BSC		
K5	0.20 BSC			0.008 BSC		
L	0.25	0.30	0.35	0.010	0.012	0.014

RECOMMENDED PAD LAYOUT FOR DFN2X2



Dimensions in mm/(Inches)

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